The thesis was devoted to the growth of high quality GaAs Solar Cells on Ge substrates using metal-organic vapor-phase epitaxy (MOVPE) technique. According to published references, a two-step growth process must be adopted to grow high quality GaAs epi-layers on Ge substrates. The two-step growth process needs a nucleation layer grown at lower temperature. In this work, the conditions of the nucleation layer, including growth temperature and thickness, were varied to study the effect on the GaAs epi-layers' quality. First, GaAs epi-layers were grown on Ge substrates with various nucleation layers. The surface flatness of GaAs epi-layers was examined with atomic force microscopy (AFM). The crystallization of GaAs epi-layers was examined with high-resolution x-ray diffractometer (HR-XRD). Finally, the samples of GaAs solar cells grown on Ge substrates with various nucleation layers were prepared to evaluate the device performance.

Keywords: MOVPE; GaAs; Ge; Nucleation layer; GaAs Solar Cell

Table of Contents

第一章 序論 1.1 前言 1.2 動機 1.3 太陽電池原理 1.4 同異質磊晶技術 1.4.1 异質磊晶 1.4.2 成核層 第二章 MOVPE系統與沉積機制介紹 2.1 有機金屬化學氣相沉積法 2.2 MOVPE系統簡介 2.2.1 反應腔 2.2.2 反應源及氣體控制 2.3 沉積機制 第三章 成長條件設計與元件製程 3.1 成長條件 3.2 量測系統介紹 3.2.1 HR-XDR 高解析光繞射儀 3.2.2 AFM 原子力顯微鏡 3.2.3 太陽光模擬器 3.3 製作元件流程 第四章 結果與討論 4.1 表面粗糙度與晶膜半高寬 4.2 成長砷化鎵太陽能電池 第五章 結論 參考文獻

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